

Mini-spectrometers

C10988MA-01 C11708MA

Ultra-compact mini-spectrometer integrating MEMS and image sensor technologies

The MS series are thumb-sized (27.6 × 16.8 × 13 mm) spectrometer heads developed for installation into mobile measurement equipment by merging our MEMS and image sensor technologies.

The MS series uses a CMOS image sensor integrated with a light receiving slit. The internal optical system is comprised of a convex lens on which a grating is formed by nanoimprint.

The result is a remarkably small size less than one-third the volume of the RC series mini-spectrometers that have already been marketed.

Features

- Thumb size: 27.6 × 16.8 × 13 mm
- Weight: 9 g
- Spectral response range: 340 to 750 nm (C10988MA-01) 640 to 1050 nm (C11708MA)
- Spectral resolution: 14 nm (C10988MA-01) 20 nm (C11708MA)
- Installation into mobile measurement equipment
- Wavelength conversion factor*1 is listed on final inspection sheet.

Applications

C10988MA-01

Color monitoring for printers and printing machines

Installation into large size display (Color control device)

C11708MA

- Fruit suger content measurement / cereal taste test
- Component analysis
- *1: A conversion factor for converting the image sensor pixel number into a wavelength is recorded in the module. A calculation factor for converting the A/D converted count into the input light intensity is not provided.

Optical characteristics

Parameter	C10988MA-01	C11708MA	Unit					
Spectral response range	340 to 750	640 to 1050	nm					
Spectral resolution (FWHM)* ²	14 max.	20 max.	nm					
Wavelength reproducibility*3	-0.5 to	o +0.5	nm					
Wavelength temperature dependence	-0.05 to	-0.05 to +0.05						
Spectral stray light*2 *4	-25	dB						

*2: Depends on the slit opening. Values were measured with the slit listed in the table "- Structure / Absolute maximum ratings".

*3: Measured under constant light input conditions

*4: When monochromatic light of the following wavelengths is input, spectral stray light is defined as the ratio of the count measured at the input wavelength, to the count measured in a region of the input wavelength ± 40 nm. C10988MA-01: 550 nm, C11708MA: 850 nm

Electrical characteristics

Parameter	Min.	Тур.	Max.	Unit
Supply voltage	4.75	5	5.25	V
Power consumption	-	30	-	mW
Video rate	0.25	-	200	kHz
Output impedance	-	150* ⁵	-	Ω

*5: An increase in the current consumption at the video output terminal also increases the chip temperature and so causes the dark current to rise. To avoid this, connect a buffer amplifier for impedance conversion to the video output terminal so that the current flow is minimized. As the buffer amplifier, use a JFET or CMOS input operational amplifier of optical input impedance.

Structure / Absolute maximum ratings

Parameter	Value	Unit
Dimensions (W \times D \times H)	27.6 × 16.8 × 13	mm
Weight	9	g
Number of pixels	256	pixels
Pixel size (H \times V)	12.5×1000	μm
Image sensor	CMOS linear image sensor	-
Slit ^{*6} (H \times V)	75 × 750	μm
NA*7	0.22	-
Operating temperature*8	+5 to +50	°C
Storage temperature*8	-20 to +70	°C

*6: Entrance slit aperture size

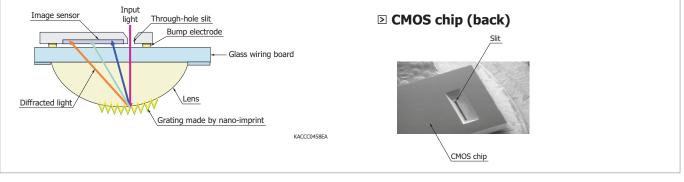
*7: Numeric aperture (solid angle)

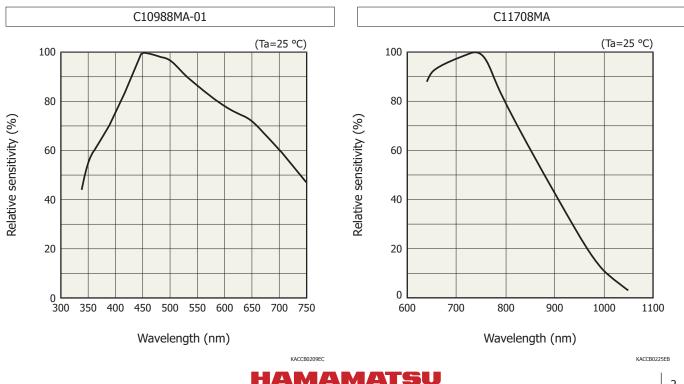
*8: No condensation

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

Optical component layout (C10988MA-01)

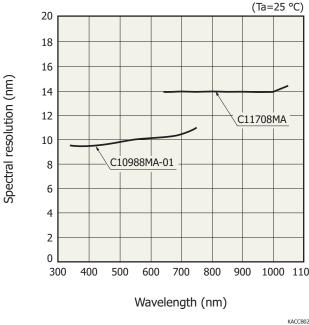
Besides a CMOS image sensor chip integrated with an optical slit by etching, the C10988MA-01 employs a grating that is formed on a convex lens by nano-imprint. This has made the unit very compact.





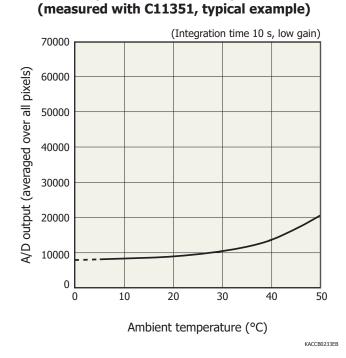
Spectral response (typical example)

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Spectral resolution vs. wavelength (typical example)

1000 1100 KACCB0211ED

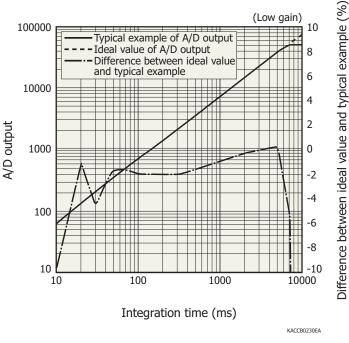


Dark output vs. ambient temperature

A/D output is the sum of the sensor and circuit offset outputs and the sensor dark output.

Linearity

(measured with C11351, typical example)



A/D output is the output with dark output is subtracted when light is input. The difference between the ideal value and typical example contains a measurement error. The smaller the A/D output, the larger the measurement error.

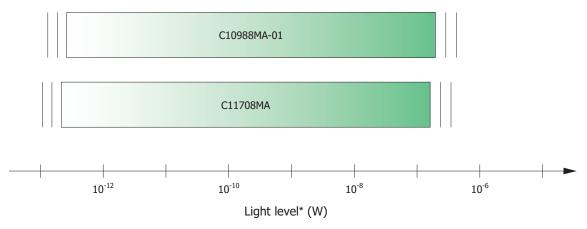
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Mini-spectrometers	MS series	C10988MA-01, C11708MA
		•=•••••

Measurable optical power

0.2

29.6



* Input spot diameter: 800 μm (C10988MA-01: $\lambda {=}550$ nm, C11708MA: $\lambda {=}850$ nm)

Dimensional outline (unit: mm, tolerance unless otherwise noted: ±0.2)

1.0 5.0 Index mark Slit 0.075 × 0.75 1.5 0.51 6 1 10 2 9 Γ 16.8 3 ¥ F 4 7 Γ 6 5 Γ 2.54 В 13 -27.6 Slit position 2.6 1 CLK ·_____ 2 GND ③ NC ④ ST 13 5 NC 6 Gain7 EOS 16 8 NC) Vdd 1.0 1 Video Weight: 9 g

C10988MA-01 C11708MA A φ3 φ2.8 B 0.75 0.5

KACCA0257EC

KACCB0210ED



Electrical connections with an external circuit

Make electrical connections to an external circuit using the lead pins.

Pin no.	Symbol	Name of pin	I/O	Description
1	CLK	Clock pulse	I	Sensor scan sync signal
2	GND	Ground		GND
3	NC			No connection
4	ST	Start pulse	I	Start pulse
5	NC			No connection
6	Gain	Gain	I	Image sensor: gain setting
7	EOS	End of scan	0	EOS (end of scan) signal
8	NC			No connection
9	Vdd	Supply voltage	I	Power supply of image sensor: 5 V
10	Video	Video output	0	Video output signal

Precation for use

• If external force is repeatedly applied to the lead pins, this may damage the lead pins. When installing this product in locations subject to vibration, secure it with resin or a holder, etc. (Recommended resin: KE347B, etc. made by Shin-Etsu Chemical Co., Ltd.)

• The sensor may be damaged by soldering, so be careful of the soldering temperature and time.

As a general guide, finish soldering within 3.5 seconds at 370 °C or less when soldering by hand, or within 10 seconds at 260 °C or less when using a solder bath.

CMOS image sensor

Recommended terminal voltage

Parameter		Symbol	Min.	Тур.	Max.	Unit
Supply voltage	Vdd	4.75	5	5.25	V	
Cain coloction terminal voltage	High gain	Gain	0	-	0.4	V
Gain selection terminal voltage	Low gain	Gain	Vdd - 0.25	Vdd	Vdd + 0.25	V
	High level		Vdd - 0.25	Vdd	Vdd + 0.25	V
Clock pulse voltage	Low level	V(CLK)	0	-	0.4	V
Start pulsa valtaga	High level	V(ST)	Vdd - 0.25	Vdd	Vdd + 0.25	V
Start pulse voltage	Low level	V(ST)	0	-	0.4	V

Electrical characteristics

Parameter		Symbol	Min.	Тур.	Max.	Unit	
Clock pulse frequency*9	f(CLK)	1	-	800	kHz		
Power concumption	High gain	D	-	-	60	m)//	
Power consumption	Low gain		-	-	60	mW	

*9: Ta=25 °C, Vdd=5 V, V(CLK)=V(ST)=5

Electrical and optical characteristics

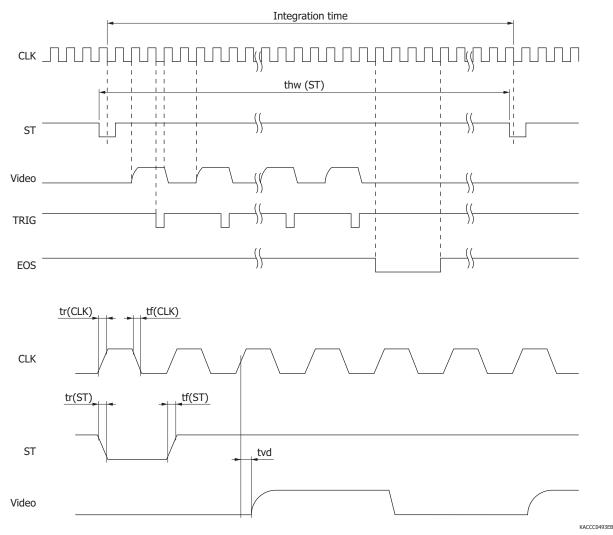
Parameter		Symbol	Min.	Тур.	Max.	Unit	
Dark current	High gain	To	-	0.02	0.08	24	
	Low gain	ID	-	0.02	0.08	рА	
Output offset voltage	High gain	Vo	0.15	0.35	0.55	V	
Output onset voltage	Low gain	VO	0.15	0.35	0.55	v	
Feedback capacitance of	High gain	Cf	-	1.4	-	рF	
charge amplifier*10	Low gain	C	-	4.8	-	pi	
Saturation output voltage*11	High gain	Vsat	2.3	2.8	3.3	V	
Saturation output voltage*11	Low gain	VSal	1.4	1.7	2.0	v	
Readout noise	High gain	Nr	-	0.3	0.5	mV rms	
	Low gain		-	0.2	0.4		

*10: Gain=5 V (low gain), Vg=0 V (high gain)

*11: Difference from Vo



Timing chart



Parameter	Symbol	Min.	Тур.	Max.	Unit
Start pulse high period	thw(ST)	1030/f (CLK)	-	-	S
Start pulse rise and fall times	tr(ST), tf(ST)	0	20	30	ns
Clock pulse duty ratio	-	45	50	55	%
Clock pulse rise and fall times	tr(CLK), tf(CLK)	0	20	30	ns
Video delay time	tvd	-	20	-	ns

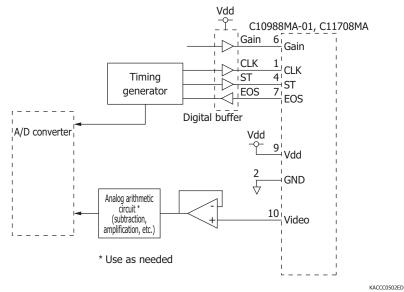
Note: The clock pulse should be set from high to low just once when the start pulse is low. The internal shift register starts operating at this timing.

The integration time is determined by the start pulse intervals. However, since the charge integration of each pixel is carried out between the signal readout of that pixel and the next signal readout of the same pixel, the start time of charge integration differs depending on each pixel. In addition, the next start pulse cannot be input until signal readout from all pixels is completed. Video output is 1/4 of the clock pulse frequency.



MS series

Recommended driver circuit example



Evaluation circuit C11351 for mini-spectrometer MS series

The C11351 is a circuit board designed to simply evaluate characteristics of minispectrometer MS series. By using the C11351 with the MS series (sold separately) and a USB cable A9160 (AB type; sold separately), the MS series characteristics can be evaluated with the evaluation software^{*12}.

Features

- Initial evaluation circuit for mini-spectrometer MS series
- Wavelength conversion factors of MS series can be input from PC*13
- High A/D resolution (16 bits)

Powered only via USB port

*12: Compatible OS: Microsoft[®] Windows[®] 7 Professional SP1 (32-bit)*¹⁴ Microsoft[®] Windows[®] 7 Professional SP1 (64-bit)*¹⁴

*13: A typical wavelength conversion factor for converting the image sensor pixel number into a wavelength is recorded in C11351. To measure a spectrum with higher wavelength accuracy, it is necessary to input the wavelength conversion factor listed in the final inspection sheet that comes with each C10988MA-01 or C11708MA.

*14: Microsoft and Windows are either registerd trademarks or trademarks of Microsoft Corporation in the United States and other countries.

Note: Since the C11351 is an evaluation circuit for the MS series, the DLL function specifications are not available to users.

Electrical characteristics

Parameter	Specification	Unit
Interface	USB 2.0	-
A/D conversion	16	bit
Clock pulse frequency	800	kHz
Video rate	200	kHz
Integration time	5 to 10000	ms





General ratings / Absolute maximum ratings

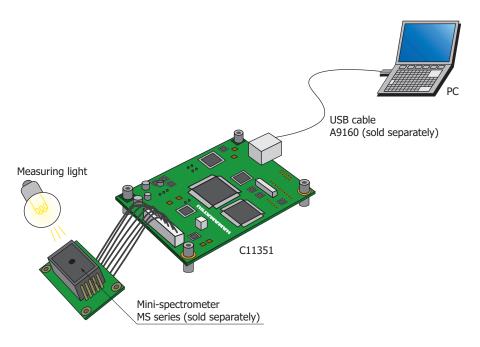
Pa	rameter	Specification	Unit			
Applicable mini-spectrometer		C10988MA-01, C11708MA	-			
Dimonsions	Control board	80 × 60	mm			
Dimensions	Sensor board	Sensor board 30 × 44				
Operation temperature*15		+5 to +40	°C			
Storage temperature*15		-20 to +70	°C			

*15: No condensation

Note: Exceeding the absolute maximum ratings even momentarily may cause a drop in product quality. Always be sure to use the product within the absolute maximum ratings.

- Connection example

Evaluation software



KACCC0494EC

55000 50000 45000 45000 Draw None MS 25rp3. Tabl. 46/4 X8-581 Bue 💌 カージルタイプ X(カージル)1 E-Fullength M X(カージル2 E-Fullength M 25000 20000 15000 0.00 ○ \$5738/4925-58000085850078 ⊙ \$5738/4925-5800085853785 波義(ne) Va A/0かいト 波長 A/0 かいト 99999 288 198 500



Mini-spectrometer lineup

•		•																								
Type no.		Туре	20	0	400	60	00	80									(nm) 1800		000	2200) 24	400	260		Spectral resolution max. (nm)	Image sensor
C10082CA		TM-UV/VIS-CCD High sensitivity																							6	Back-thinned type
C10082CAH	1	TM-UV/VIS-CCD High resolution		2	00 t	:0 8	00																	ŀ	1*	CCD image senso
C10082MD	s	TM-UV/VIS-MOS Wide dynamic range																						ŀ	6	CMOS linear image sensor
C10083CA	series	TM-VIS/NIR-CCD High sensitivity																							8 (λ=320 to 900 nm)	Back-thinned type
C10083CAH	μ	TM-VIS/NIR-CCD High resolution																						ŀ	1* (λ=320 to 900 nm)	CCD image senso
C10083MD	-	TM-VIS/NIR-MOS Wide dynamic range			3	20	to 1	100	0																8	CMOS linear image sensor
C11697MA	1	TM-VIS/NIR-MOS-II Trigger-compatible																						ŀ	8	CMOS image sense with amp array
C9404CA		TG-UV-CCD High sensitivity						1													1				3	Back-thinned type CCD image sense
C9404CAH	_ 	TG-UV-CCD High resolution		200 to 4	00																			ŀ	1*	Back-thinned typ CCD image sense
C9405CB	series	TG-SWNIR-CCD-II IR-enhanced					500	to	11	00															5 (λ=550 to 900 nm)	IR-enhanced back-thinned CC image sensor
C11713CA	٩	TG-RAMAN-I High resolution					50)0 t	:0 6	500															0.3*	Back-thinned typ CCD image sense
C11714CA	1	TG-RAMAN-II High resolution								79	0 to	0 92	20												0.3*	Back-thinned typ CCD image sense
NEW C11482GA		TG2-NIR Non-cooled type																							7	
C9913GC	series	TG-cooled NIR-I Low noise (cooled type)								Т	90	00 te	01	.700)									ľ	7	InGaAs linear
C9914GB	TG se	TG-cooled NIR-II Low noise (cooled type)												11	00	to 2	2200)							8	image sensor
C11118GA		TG-cooled NIR-III Low noise (cooled type)													900	0 tc	25	50							20	
C11007MA	series	RC-VIS-MOS Spectrometer module			340	to	780																		9	CMOS linear image sensor
C11008MA	RC se	RC-SWNIR-MOS Spectrometer module					64	0 to	o 1(050															8	IR-enhanced CMOS linear image sensor
Тур.		•									1			1							-1					
For installation int	o mot	pile measuring eq	uipm	nent			_																		Creatural recolution	
Type no.		Туре	20	0 4	100	60	00	800									(nm) 1800		00	2200	24	100	260		Spectral resolution max. (nm)	Image senso
C11009MA	series	RC-VIS-MOS Spectrometer head		[340) to	780)																	9	CMOS linear image sensor
C11010MA	RC se	RC-SWNIR-MOS Spectrometer head					64	0 to	o 1	050															8	IR-enhanced CMOS linear image sensor
Ultra-compact typ	e for i	installation into m	obile	e me	easu	ring	equ	uipr	ner	nt																
Type no.		Туре	20	0	400	60	00	80									(nm) 1800		000	2200) 24	400	260	- I	Spectral resolution max. (nm)	Image sensor
NEW C10988MA-01	ries	MS-VIS-MOS Spectrometer head		[340	to	750																		14	CMOS linear

Type no.		Туре		400	600	800		1200		· ·	2200	2400	2600	max. (nm)	Image sensor
NEW C10988MA-01	eries	MS-VIS-MOS Spectrometer head		340	to 75	0								14	CMOS linear image sensor
C11708MA	MS S6	MS-SWNIR-MOS Spectrometer head			6	40 to	1050							20	



Related information

www.hamamatsu.com/sp/ssd/doc_en.html

- Precautions
 - Notice
- Technical information
 - · Mini-spectrometer / Technical information

Information described in this material is current as of October, 2014.

Product specifications are subject to change without prior notice due to improvements or other reasons. This document has been carefully prepared and the information contained is believed to be accurate. In rare cases, however, there may be inaccuracies such as text errors. Before using these products, always contact us for the delivery specification sheet to check the latest specifications.

The product warranty is valid for one year after delivery and is limited to product repair or replacement for defects discovered and reported to us within that one year period. However, even if within the warranty period we accept absolutely no liability for any loss caused by natural disasters or improper product use.

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